								REV	ISIO	N REC		-	10, 11							
REV								DES	CRIP	TION									DAT	
0			ELEASE																06/12	
А			ECTION "9.98 V"				10, DM-10, OUTPUT VOLTAGE, 100 KRAD MINIMUM LIMIT AGE 10.								02/28	8/97				
В	<ul> <li>PAGE 2, ADDED PARAGRAPHS 3.2.1, 3.2.2, AND 3.2.3. PARAGRAPH 3.3.b, ADDED "(SEE PARAGRAPH 3.2)".</li> <li>PAGE 4, PARAGRAPH 3.12, WAFER LOT ACCEPTANCE REDEFINED. PARAGRAPH 4.4.2, GROUP B INSPECTION, REDEFINED. PARAGRAPH 4.4.3, GROUP D INSPECTION,</li> </ul>										11/25	5/97								
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			5, PARA	GRAP	H 4.5	. SOU	RCE I	NSPE	CTIO	N. REI	DEFIN	ED.								
			6, FIGUR							-										
С	•	PAGE	4, AMEN STROPH	IDED	PAR/	AGRA				~			PTION	TO A	NAL	YSIS (	OF		05/8	/98
D			6, FIGUR				Jja FR	OM 18	80°C/	W TO	150°C	/W.							11/17	7/99
E	•	PAGE AS SPI PARAC PAGE PARAC PARAC IIA OF PARAC	4, PARA ECIFIED GRAPH 3 5, PARA GRAPH 4 GRAPH 4 MIL-STI GRAPH 4 L-STD-88	GRAP IN TA 3.9, AI GRAP I.4.1, A I.4.2.2 D-883 I.4.3.2	PH 3.7 ABLE DDED PH 4.3 ADDE , CHA " TO ' , CHA	, CHA III HE "HER , ADD D "HE NGEI "ALL I NGEI	NGEI REIN" ED "H EREIN D VER FOOT D VER	O VER ", LIN AFTE IEREI " AFT BIAG NOTE BIAG	BIAG E 2. R "TA N" AI E R " E IN I S PEI E IN I	E FRO ABLE I FTER ' FABLI LINE I RTAIN LINE I	OM "SI II", LII "TABI E III", 1 I FROI IING T I FROI	PECII NE 2. LE III' LINE M "AI O TA M "AI	", LINI 2. LL FO ABLE I LL FO	E 2. OTNO IA IN OTNO	OTES ( MIL-S OTES (	DF TA STD-8 DF TA	BLE 83".	V	12/13	
F			3, PARA																06/25	5/00
	• • • • • •	PARAC PARAC PARAC PAGE PAGE PAGE PAGE PAGE PAGE PAGE 10.008	4, PARA GRAPH 3 GRAPH 3 GRAPH 3 GRAPH 3 8, ADDE 9, CHAN 10, ADD 11, CHAN 12, ADD 13, CHAN 15, CHAN	3.10.1, 3.10.2, 3.10.3, 3.11.3, D PAG GED I ED DI NGED NGED NGED DDED	ADD CHA CHA GE 7 I FIGU FIGU FIGU FIGU FIGU FIGU VOUT	ED FI NGED NGED NGED DEVIC RE 2 T E OPT JRE 3 E OPT JRE 4 OUT BIAGE	GURE VER FIGU CE OP TO 3. ION 4 TO 5. ION 4 TO 7. PUT V E TO N	22. BIAGI BIAGI JRE 4 TION , FIGU , FIGU VOLTA NOTE :	E ADI E. TO 7. 4, PA JRE 4 JRE 6 AGE 1 3.	DED F CKAG TERM BURN 0 KRA	IGURI E OU IINAL J-IN C AD (SI)	ES 3 A FLINI CON IRCU ) MIN	AND 4. E. INECT IT. TO 9.	IONS. 992 A	ND M					
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REV	REVISION RECORD DESCRIPTION	DATE
G	• PAGE 8, CHANGED THETA JA TO $\theta_{ja} = +170^{\circ}$ C/W AND THETA JC TO $\theta_{jc} = +40^{\circ}$ C/W FROM $\theta_{ja}$	9/05/00
	= 225°C/W AND θjc 18°C/W PER PACKAGE ENGINEERING.	
Н	CONVERSION FROM WORD PERFECT TO MICROSOFT WORD. REDUCED SPEC PAGES TO	03/26/02
	14 TOTAL.	
	PAGE 2, AN ADDITIONAL REVISION RECORD PAGE WAS INSTALLED	
	MADE THE REVISION RELEASE DATES AND THE DOCUMENT CONTROL HISTORY PAGE	
	DATE MATCH	
	• PAGE 3:	
	PARAGRAPH 3.2.1 THROUGH 3.2.4, ADDED THE WORD "OPTION" PRECEDING THE NUMBER OF EACH LTC PART NUMBER FOR BETTER CUSTOMER ORDERING CONVENIENCE.	
	<ul> <li>PAGE 4:</li> </ul>	
	• FAGE 4. PARAGRAPH 3.6, CHANGED "TABLE IA" TO "TABLE II"	
	PARAGRAPH 3.7, CHANGED "TABLE III" TO "TABLE II"	
	PARAGRAPHS 3.8.1 AND 3.8.2, ADDED THE PACKAGE TYPES AND OPTIONS AFTER EACH	
	FIGURE.	
	PARAGRAPH 3.9, CHANGED "TABLE II" TO "TABLE III"	
	PARAGRAPHS 3.10.1 AND 3.10.2, ADDED THE PACKAGE TYPES AFTER EACH FIGURE	
	PARAGRAPH 3.11.1 WAS CHANGED FROM "dosage rate of approximately 20 Rads per	
	second" TO "dosage rate of less than or equal to 10 Rads per second"	
	• PAGE 5:	
	PARAGRAPHS 4.1 THROUGH 4.4.2.1 CHANGES WERE DONE TO CLARIFY GROUP SAMPLING.	
	• PAGE 6:	
	PARAGRAPH 4.4.3 CHANGE WAS DONE TO CLARIFY GROUP SAMPLING. PARAGRAPHS 4.6.2 THROUGH 4.6.4 WERE RE-WRITTEN. THESE DATA PROVIDED, AND DATA	
	AVAILABLE.	
	PARAGRAPH 4.6.10 NOTE, ADDED FURTHER EXPLANATION OF MINIMUM DELIVERED DATA.	
	PAGES 7 THROUGH 12, ALL FIGURE TITLES CHANGED TO HAVE DEVICE OPTIONS AND	
	PACKAGE TYPES AT TOP OF PAGE, AND HAVE ALL FIGURES AT BOTTOM OF PAGE.	
	• PAGE 9, MOVED FIGURE 4 TO PAGE 9 FROM PAGE 10 AS SHOWN IN PREVIOUS	
	SPECIFICATION REVISION.	
	• PAGE 12, FIGURE 7, TOTAL DOSE BIAS CIRCUIT REVISED BY ENGINEERING.	
	• PAGE 13, TABLES I, II AND CORRESPONDING NOTES ALL ON ONE PAGE.	
J	• PAGE 8, CHANGED OUTLINE DRAWING PIN 1 NOTCH MOVED TO INSIDE LEAD	05/19/03
	LOCATION.	
Κ	• PAGE 4, CHANGED INITIAL RATE OF RADS TO 240 RADS/SEC.	03/15/05
L	PAGE 4, ADDED NOTE: ABSOLUTE MAXIMUM RATINGS ARE THOSE VALUES BEYOND	08/15/05
	WHICH THE LIFE OF A DEVICE MAY BE IMPAIRED.	
М	• PAGE 5, CHANGED IN BOTH PARAGRAPHS 4.2, 4.3 IN CONJUNCTION TO 3.3 CHANGED TO	12/07/07
	3.4 AND PARAGRAPH 4.3 CHANGED 3.1.1 TO 3.1 AND 3.2.1 TO 3.1.1	
Ν	• PAGE 4, PARAGRAPH 3.11.1 CHANGED VERBIAGE.	04/30/08
Р	• PAGE 5, PARAGRAPH 4.4.2 CHANGED VERBIAGE.	07/18/08
	• PAGE 8, FIGURE 2 NOTE 2 ADDED TO LEAD THICKNESS. DATA SHEET CHANGE TO	
	ELECTRICAL TEST NOTES #7, #9 $V_{IN}$ = 12V CHANGED TO $V_{IN}$ = 15V.	
Q	ADD MAXIMUM JUNCTION TEMPERATURE 150°C TO SECTION 3.4	08/10/18
	CHANGED CAGE CODE FROM 94155 TO 64155	
	• CHANGED LINEAR TECH FOOTER TO ANALOG DEVICES INC.	
R	TO CHANGE LINEAR TO ANALOG AND REMOVE SOURCE	3/23/21
S	• The RH1021DMH-10 was OBS	<mark>9/21/21</mark>

- 1.0 SCOPE:
  - 1.1 This specification defines the performance and test requirements for a microcircuit processed to a space level manufacturing flow.
- 2.0 APPLICABLE DOCUMENTS:
  - 2.1 <u>Government Specifications and Standards</u>: the following documents listed in the Department of Defense Index of Specifications and Standards, of the issue in effect on the date of solicitation, form a part of this specification to the extent specified herein.

**SPECIFICATIONS:** 

MIL-PRF-38535	Integrated Circuits (Microcircuits) Manufacturing, General Specification for
MIL-STD-883	Test Method and Procedures for Microcircuits
MIL-STD-1835	Microcircuits Case Outlines

- 2.2 <u>Order of Precedence</u>: In the event of a conflict between the documents referenced herein and the contents of this specification, the order of precedence shall be this specification, MIL-PRF-38535 and other referenced specifications.
- 3.0 REQUIREMENTS:
  - 3.1 <u>General Description</u>: This specification details the requirements for the RH1021-10, Precision 10V Reference, processed to space level manufacturing flow.
  - 3.2 <u>Part Number</u>:
    - 3.2.1 Option 1 RH1021BMH-10 (TO5 Metal Can, 8 Leads)
    - 3.2.2 Option 2 RH1021CMH-10 (TO5 Metal Can, 8 Leads)
    - 3.2.3 Option 3 RH1021DMH-10 OBS (TO5 Metal Can, 8 Leads)
    - 3.2.4 Option 4 RH1021CMW-10 (Glass Sealed Flatpack, 10 Leads)

#### 3.3 <u>Part Marking Includes</u>:

- 3.3.1 LTC Logo
- 3.3.2 LTC Part Number (See Paragraph 3.2)
- 3.3.3 Date Code
- 3.3.4 Serial Number
- 3.3.5 ESD Identifier per MIL-PRF-38535, Appendix A

#### 3.4 <u>The Absolute Maximum Ratings</u>:

Input Voltage	40V
Input / Output Voltage Differential	
Output to Ground Voltage	
(Shunt Mode Current Limit)	16V
Trim Pin to Ground Voltage	
Positive	Equal to $V_{OUT}$
Negative	-20V
Output Short Circuit Duration	
$V_{IN} = 35V$	10 sec
$V_{\rm IN}{=}{\leq}20V\qquad .\qquad .\qquad$	Indefinite
Operating Temperature Range	-55°C to 125°C
Maximum Junction Temperature	150°C
Storage Temperature Range	-65°C to 150°C
Lead Temperature (Soldering, 10 sec.)	300°C
<b>NOTE:</b> Absolute maximum ratings are those values beyond which may be impaired.	ch the life of a device
Electrostatic discharge sensitivity, ESDS, shall be Class 1.	

- 3.6 <u>Electrical Performance Characteristics</u>: The electrical performance characteristics shall be as specified in **Table I** and **Table II**.
- 3.7 <u>Electrical Test Requirements</u>: Screening requirements shall be in accordance with 4.1 herein, MIL-STD-883, Method 5004, and as specified in **Table IV** herein.
- 3.8 <u>Burn-In Requirement</u>:

3.5

- 3.8.1 Options 1, 2, 3 (TO5): Static Burn-In, Figure 5
- 3.8.2 Option 4 (Glass Sealed Flatpack) : Static Burn-In, Figure 6
- 3.9 <u>Delta Limit Requirement</u>: Delta limit parameters are specified in **Table III** herein, are calculated after each burn-in, and the delta rejects are included in the PDA calculation.
- 3.10 <u>Design, Construction, and Physical Dimensions</u>: Detail design, construction, physical, dimensions, and electrical requirements shall be as specified herein.
  - 3.10.1 Mechanical / Packaging Requirements: Case outlines and dimensions are in accordance with Figure 1 (TO5/8 Leads) and Figure 2 (Glass Sealed Flatpack/10 Leads).
  - 3.10.2 Terminal Connections: The terminal connections shall be as specified in Figure 3 (TO5/8 Leads) and Figure 4 (Glass Sealed Flatpack/10 Leads).
  - 3.10.3 Lead Material and Finish: The lead material shall be Kovar for TO5 and alloy 42 for flatpack. The lead finish shall be hot solder dip (Finish letter A) in accordance with MIL-PRF-38535.
- 3.11 <u>Radiation Hardness Assurance (RHA)</u>:

## SPEC NO. 05-08-5018 REV. S

- 3.11.1 The manufacturer shall perform a lot sample test as an internal process monitor for total dose radiation tolerance. The sample test is performed with MIL-STD-883 TM1019 Condition A as a guideline.
- 3.11.2 For guaranteed radiation performance to MIL-STD-883, Method 1019, total dose irradiation, the manufacturer will provide certified RAD testing and report through an independent test laboratory when required as a customer purchase order line item.
- 3.11.3 Total dose bias circuit is specified in **Figure 7**.
- 3.12 <u>Wafer Lot Acceptance</u>: Wafer lot acceptance shall be in accordance with MIL-PRF-38535, Appendix A, except for the following: Topside glassivation thickness shall be a minimum of 4KÅ.
- 3.13 <u>Wafer Lot Acceptance Report</u>: SEM is performed per MIL-STD-883, Method 2018 and copies of SEM photographs shall be supplied with the Wafer Lot Acceptance Report as part of a Space Data Pack when specified as a customer purchase order line item.
- 4.0 VERIFICATION (QUALITY ASSURANCE PROVISIONS)
  - 4.1 <u>Quality Assurance Provisions</u>: Quality Assurance provisions shall be in accordance with MIL-PRF-38535. Analog Devices is a QML certified company, and all Rad Hard candidates are assembled on qualified Class S manufacturing lines.
  - 4.2 <u>Sampling and Inspection</u>: Sampling and Inspection shall be in accordance with MIL-STD-883, Method 5005 with QML allowed and TRB approved deviations in conjunction with paragraphs 3.1.1, 3.2.1, and 3.4 of the test method.
  - 4.3 <u>Screening</u>: Screening requirements shall be in accordance with MIL-STD-883, Method 5004 with QML allowed and TRB approved deviations in conjunction with paragraphs 3.1, 3.1.1, and 3.4 of the test method. Electrical testing shall be as specified in **Table IV** herein.
    - 4.3.1 Analysis of catastrophic (open/short) failures from burn-in will be conducted only when a lot fails the burn-in or re-burn-in PDA requirements.
  - 4.4 <u>Quality Conformance Inspection</u>: Quality conformance inspection shall be in accordance with 4.2 and 4.3 herein and as follows:
    - 4.4.1 Group A Inspection: Group A inspection shall be performed in accordance with 4.1 herein, per MIL-STD-883, Method 5005, and specified in **Table IV** herein.
    - 4.4.2 Group B Inspection: When purchased, a full Group B is performed on an inspection lot. As a minimum, Subgroups 1-4 plus 6 are performed on every assembly lot, and Subgroup B2 (Resistance to Solvents / Mark Permanency) and Subgroup B3 (Solderability) are performed prior to the first shipment from any inspection lot and Attributes provided when a Full Space Data Pack is ordered. Subgroup B5 (Operating Life) is performed on each wafer lot. This subgroup may or may not be from devices built in the same package style as the current inspection lot. Attributes and variables data for this subgroup will be provided upon request at no charge.

4.4.2.1	Group B, Subgroup $2c = 10\%$	Group B, Subgroup 5 = *5% (*per wafer or inspection lot
	Group B, Subgroup $3 = 10\%$	whichever is the larger quantity)
	Group B, Subgroup $4 = 5\%$	Group B, Subgroup 6 = 15%

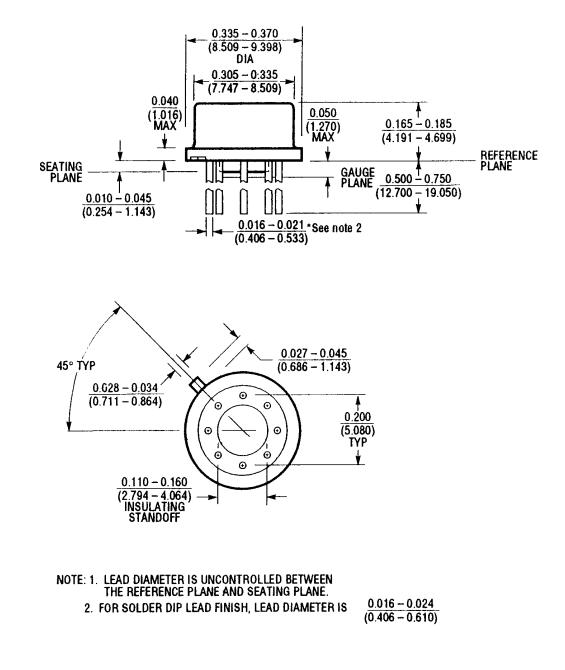
4.4.2.2 All footnotes pertaining to Table IIa in MIL-STD-883, Method 5005 apply. The quantity (accept number) of all other subgroups are per MIL-STD-883, Method 5005, Table IIa.

- 4.4.3 Group D Inspection: When purchased, a full Group D is performed on an inspection lot. As a minimum, periodic full Group D sampling is performed on each package family for each assembly location every 26 weeks. A generic Group D Summary is provided when a full Space Data Pack is ordered.
  - 4.4.3.1 Group D, Subgroups 3, 4 and 5 = 15% each.
  - 4.4.3.2 All footnotes pertaining to Table IV in MIL-STD-883, Method 5005 apply. The quantity (accept number) or sample number and accept number of all other subgroups are per MIL-STD-883, Method 5005, Table IV.
- 4.5 <u>Deliverable Data</u>: Deliverable data that will ship with devices when a Space Data Pack is ordered:
  - 4.5.1 Lot Serial Number Sheets identifying all devices accepted through final inspection by serial number.
  - 4.5.2 100% attributes (completed lot specific traveler; includes Group A Summary)
  - 4.5.3 Burn-In Variables Data and Deltas (if applicable)
  - 4.5.4 Group B2, B3, and B5 Attributes (Variable's data, if performed on lot shipping)
  - 4.5.5 Generic Group D data (4.4.3 herein)
  - 4.5.6 SEM Photographs (3.13 herein)
  - 4.5.7 Wafer Lot Acceptance Report (3.13 herein)
  - 4.5.8 X-Ray Negatives and Radiographic Report
  - 4.5.9 A copy of outside test laboratory radiation report if ordered
  - 4.5.10 Certificate of Conformance certifying that the devices meet all the requirements of this specification and have successfully completed the mandatory tests and inspections herein.

Note: Items 4.5.1 and 4.5.10 will be delivered as a minimum, with each shipment. This is noted on the Purchase Order Review Form as "No Charge Data".

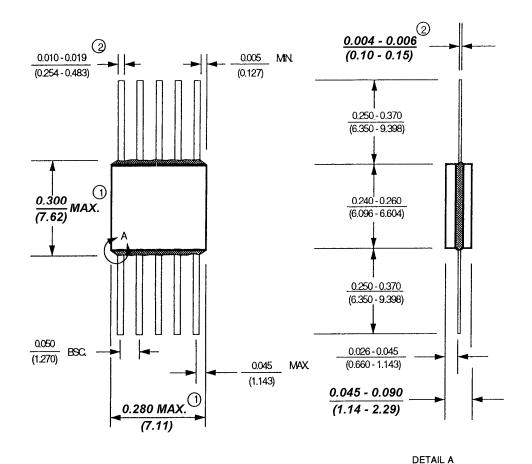
5.0 <u>Packaging Requirements</u>: Packaging shall be in accordance with Appendix A of MIL-PRF-38535. All devices shall be packaged in conductive material or packaged in anti-static material with an external conductive field shielding barrier.

## DEVICE OPTIONS 1, 2, 3 TO5 METAL CAN / 8 LEADS CASE OUTLINE



 $\theta ja = +150^{\circ}C/W$  $\theta jc = +40^{\circ}C/W$ 

DEVICE OPTION 4 W10, GLASS SEALED FLATPACK / 10 LEADS CASE OUTLINE



NOTE: 1. THIS DIMENSION ALLOWS FOR OFF-CENTER LID, MENISCUS AND GLASS OVER RUN.

NOTE: 2. INCREASE DIMENSION BY 0.003 INCH WHEN LEAD FINISH IS APPLIED (SOLDER DIPPED).

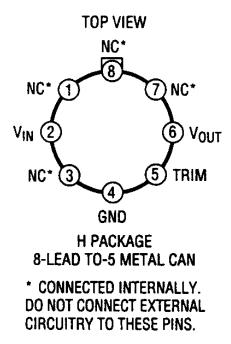
θja = +170°C/W θjc = +40°C/W

FIGURE 2

<u>0.005</u> MIN. (0.127)

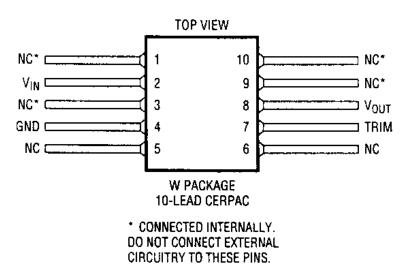
<u>0.008 - 0.015</u> (0.203 - 0.381)

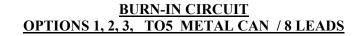
## TERMINAL CONNECTIONS DEVICE OPTIONS 1, 2, 3, TO5 METAL CAN / 8 LEADS

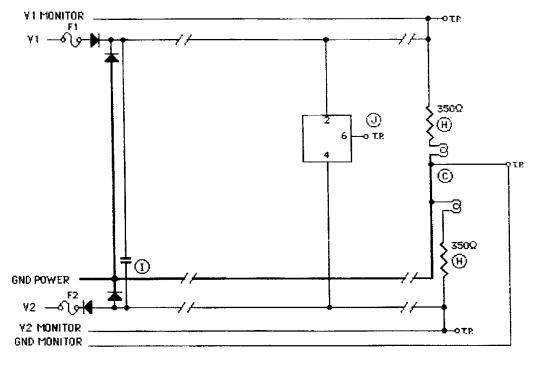


# FIGURE 3

## **OPTION 4, GLASS SEALED FLATPACK / 10 LEADS**



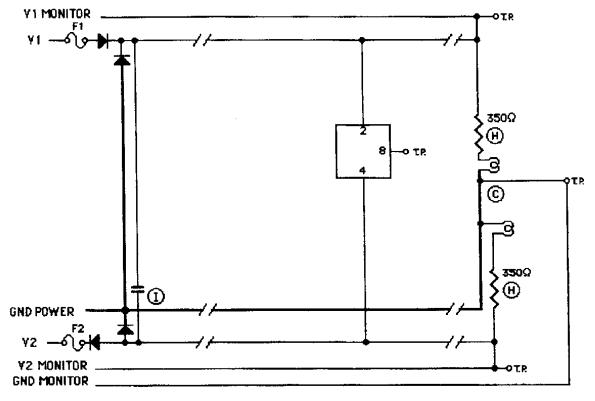




NOTES:

- 1. Unless otherwise specified, component tolerances shall be per military specification.
  Tj = 168 °C maximum.
- 3. Ta = 150 °C.
- 4. Burn-in Voltages: V1 = +20V to +22V Y2 = -20Y to -22Y

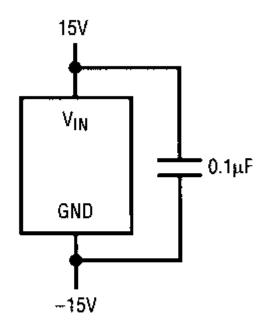
**BURN-IN CIRCUIT OPTION 4, GLASS SEALED FLATPACK / 10 LEADS** 



## NOTES:

- 1. Unless otherwise specified, component tolerances shall be per military specification. 2. Tj =  $168 \,^{\circ}$ C maximum.
- 3. Ta = 150°C.
- 4. Burn-in Yoltages: Y1 = +20Y to +22Y Y2 = -20Y to -22Y

# TOTAL DOSE BIAS CIRCUIT



				T	a = 25	°C	SUB-	-55°C	$\leq T_A \leq 125^{\circ}C$	SUB-	[
SYMBOL	PARAMETER	CONDITIONS	NOTES	MIN	TYP	MAX	GROUP	MIN	TYP MAX	GROUP	UNITS
Vout	Output Voltage	RH1021CM-10 RH1021BM-10, DM-10	1	9.995 9.95		10.005 10.05	1				v v
TCV <sub>OUT</sub>	Output Voltage Temperature Coefficient	RH1021BM-10 RH1021CM-10, DM-10	2 2						5 20	2,3 2,3	ppm/°C ppm/°C
$\frac{\Delta V_{0UT}}{\Delta V_{N}}$	Line Regulation	$11.5V \le V_{IN} \le 14.5V$ $14.5V \le V_{IN} \le 40V$	3 3			4 2	1 1		6 4	2,3 2,3	ppm/V ppm/V
ΔV <sub>OUT</sub> Δl <sub>out</sub>	Load Regulation (Sourcing Current)	0 ≤ I <sub>OUT</sub> ≤ 10mA	3			25	1		40	2,3	ppm/mA
	Load Regulation (Shunt Mode)	$1.7$ mA $\leq I_{OUT} \leq 10$ mA	3,4			100	1		150	2,3	ppm/mA
Is	Supply Current (Series Mode)			1		1.7	1		2.0	2,3	mA
IMIN	Minimum Current (Shunt Mode)	V <sub>IN</sub> is Open				1.5	1		1.7	2,3	mA
· · · · ·	Output Voltage Noise	0.1Hz ≤ f ≤ 10Hz 10Hz ≤ f ≤ 1kHz	5 5		6	6	4				μVp-p μVrms
	Long-Term Stability of V <sub>OUT</sub>	ΔT = 1000 Hrs Noncumulative	6		15						ppm
	Temperature Hysteresis of V <sub>OUT</sub>	ΔT = ±25°C			5						ppm

## TABLE I: ELECTRICAL CHARACTERISTICS (PRE-IRRADIATION) NOTE 9

#### **TABLE II: ELECTRICAL CHARACTERISTICS (POST-IRRADIATION) NOTE 7**

CVMDOL	DADAMETED	CONDITIONS	NOTES	10Kra MIN	ad(Si) MAX	20Kr: Min	ad(Si) MAX	50Kr Min	ad(Si) MAX	100Kr MIN	ad(Si) MAX	200Ki Min	rad(Si) MAX	UNITS
STMBUL	PARAMETER	COMDITIONS	NUIES	IAILM	MIAA	MIN	ITIAA	14110	ITIMA			171114	INAA	
V <sub>OUT</sub>	Output Voltage	RH1021CM-10 RH1021BM-10, DM-10	1 1	9.992 9.95	10.008 10.05	9.99 9.945	10.01 10.055		10.013 10.06	9.985 9.938	10.015 10.06		10.02 10.065	V V
TCV <sub>OUT</sub>	Output Voltage Temperature Coefficient	RH1021BM-10 RH1021CM-10, DM-10	2 2		5 20		5 20		5 20		7 22		10 25	ppm/°C ppm/°C
$\frac{\Delta V_{0UT}}{\Delta V_{IN}}$	Line Regulation	$\begin{array}{l} 11.5V \leq V_{IN} \leq 14.5V \\ 14.5V \leq V_{IN} \leq 40V \end{array}$	3 3		4 2		4 2		4.5 2		5 2		6 3	ppm/V ppm/V
ΔV <sub>OUT</sub> ΔI <sub>OUT</sub>	Load Regulation (Sourcing Current)	0 ≤ I <sub>OUT</sub> ≤ 10mA	3,8		25		25		25		25		25	ppm/mA
	Load Regulation (Shunt Mode)	1.7mA ≤ I <sub>OUT</sub> ≤ 10mA	3,4		100		100		100		100		150	ppm/mA
I <sub>MIN</sub>	Minimum Current (Shunt Mode)	V <sub>IN</sub> Is Open			1.5		1.5		1.5		1.5		1.5	mA
I <sub>S</sub>	Supply Current (Series Mode)				1.7		1.7		1.7		1.7		1.7	mA

Note 1: Output voltage is measured immediately after turn-on. Changes due to chip warm-up are typically less than 0.005%.

**Note 2:** Temperature coefficient is measured by dividing the change inoutput voltage over the temperature range by the change in temperature. Separate tests are done for hot and cold;  $T_{MIN}$  to 25°C and 25°C to  $T_{MAX}$ . Incremental slope is also measured at 25°C.

**Note 3:** Line and load regulation are measured on a pulse basis. Output changes due to die temperature change must be taken into account separately. Package thermal resistance is 150°C/W for the TO-5 (H) package and 170°C/W for the 10-lead flatpack (W) package.

**Note 4:** Shunt mode regulation is measured with the input open. With the input connected, shunt mode current can be reduced to 0mA. Load regulation will remain the same.

**Note 5:** RMS noise is measured with a 2-pole highpass filter at 10Hz and a 2-pole lowpass filter at 1kHz. The resulting output is full wave rectified and then integrated for a fixed period, making the final reading an average as opposed to RMS. Correction factors are used to convert from average to RMS and to correct for the nonideal bandpass of the filters. Peak-to-peak noise is measured with a single highpass filter at 0.1Hz and a 2-pole lowpass filter at 10Hz. The unit is enclosed in a still-air environment to eliminate thermocouple effects on the leads. Test time is 10 seconds. **Note 6:** Consult factory for units with long term stability data.

**Note 7:**  $V_{IN} = 15V$ ,  $I_{OUT} = 0$ ,  $T_A = 25^{\circ}$ C, unless otherwise noted. **Note 8:**  $I_{OUT(MAX)}$  (Sourcing) is 5mA for exposures greater than 100Krad (Si).

**Note 9:**  $V_{IN} = 15V$ ,  $I_{OUT} = 0$ , unless otherwise noted.

**Note 10:** Absolute Maximum Ratings are those values beyond which the life of a device may be impaired.

# TABLE III: POST BURN-IN ENDPOINTS AND DELTA LIMIT REQUIREMENTS $T_A = 25^{\circ}C$

## APPLIES TO RH1021BM-10 AND RH1021DM-10

	ENDPOI	NT LIMIT	DEI	LTA	
PARAMETER	MIN	MAX	MIN	MAX	UNITS
V <sub>OUT</sub>	9.95	10.05	-0.003	0.003	V

#### **APPLIES TO RH1021CM-10**

	ENDPOINT LIMIT		DEI		
PARAMETER	MIN	MAX	MIN	MAX	UNITS
V <sub>OUT</sub>	9.995	10.005	-0.003	0.003	V

## TABLE IV: ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUP
Final Electrical Test Requirements (Method 5004)	1*,2,3,4
Group A Test Requirements (Method 5005)	1,2,3,4
Group B and D for Class S, and Group C and D for Class B End Point Electrical Parameters (Method 5005)	1,2,3

\* PDA Applies to subgroup 1. See PDA Test Notes.

#### **PDA Test Notes**

The PDA is specified as 5% based on failures from group A, subgroup 1, tests after cooldown as the final electrical test in accordance with method 5004 of MIL-STD-883. The verified failures of group A, subgroup 1, after burn-in divided by the total number of devices submitted for burn-in in that lot shall be used to determine the percent for the lot.

Linear Technology Corporation reserves the right to test to tighter limits than those given.